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**(54) POLISHING COMPOSITION FOR CHEMICAL  
MECHANICAL POLISHING**

(57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a polishing composition capable of keeping high flatness of a metal surface polished by chemical mechanical polishing (CMP) and a polishing composition for two-stage polishing achieving high polishing speed ratio between the copper layer in the first stage polishing and the bar-

rier layer in the second stage polishing to enable the selective polishing of the copper layer.

**SOLUTION:** The invention provides a polishing composition for CMP (chemical mechanical polishing) containing a hydroxyalkane sulfonic acid fatty acid ester and a polishing composition for CMP containing 0.0001-10 mass% hydroxyalkane sulfonic acid fatty acid ester in the total polishing composition.

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